

[WeA3] Advanced Growth Techniques - II

Session Date	July 15 (Wed.), 2026
Session Time	15:35–17:05
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Yong-Ho Ra (Jeonbuk National University, Korea), Prof. Si-Young Bae (Pukyong National University, Korea)

[WeA3-1] [Invited]

15:35–16:05

Epitaxial Growth of III-Nitride Semiconductors and Their LED Structures

Zhe Zhuang, Yimeng Sang, and Bin Liu, Nanjing University, China

[WeA3-2]

16:05–16:20

Applications of Mist Chemical Vapor Deposition in the Deposition of Inorganic Functional Thin Films

Zaichun Sun and Bingchu Mei, Wuhan University of Technology, China

[WeA3-3]

16:20–16:35

Hybrid 3D/2D Growth Mode for High-Quality AlN on Si(111) by MOCVD

Mingtao Nong¹, Haicheng Cao¹, Tingang Liu¹, Patsy A Miranda Cortez¹, Glen Isaac Maciel García¹, Xiao Tang², Che-Hao Liao³, Kexin Ren¹, Zixian Jiang¹, and Xiaohang Li¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²University of Bristol, United Kingdom, ³National Yunlin University of Science and Technology, Taiwan

[WeA3-4]

16:35–16:50

Novel MOCVD Selective Area Growth of InGaAs/GaAs/AlGaAs Using SOI Shadow Mask and Its Application to COMD Free 980nm Laser

Akihiko Kasukawa¹, I. Novitasari¹, Z-J. Sun¹, A. Albert¹, S. L. Lee¹, and M. Arai², ¹National Taiwan University of Science and Technology, Taiwan, ²University of Miyazaki, Japan

Formation Mechanisms of Cubic GaN Grown in Si Inverted Pyramids by Selective Area OMVPE

David A. Lister, Cyan Kim, Melissa Radford, Sarah Fortin, Karen L. Kavanagh, and Simon Watkins,
Simon Fraser University, Canada